

MINI ANALOG SERIES FOR AUTOMOTIVE 105°C OPERATION LOW INPUT OFFSET VOLTAGE CMOS OPERATIONAL AMPLIFIER

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Rev.1.0_01

The mini-analog series is a group of ICs that incorporate a general purpose analog circuit in a small package. The S-19611A is an auto-zero operation, zero-drift operational amplifier that has input and output of low input offset voltage and Rail-to-Rail*1. The S-19611A is suitable for applications requiring less offset voltage. The S-19611A is a dual operational amplifier (with 2 circuits).

*1. Rail-to-Rail is a trademark of Motorola, Inc.

Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product in the purpose, contact to SII Semiconductor Corporation is indispensable.

■ Features

- Low input offset voltage: $V_{IO} = 17 \mu\text{V max. (Ta = +25}^\circ\text{C)}$
 $V_{IO} = 100 \mu\text{V max. (Ta = -40}^\circ\text{C to +105}^\circ\text{C)}$
- Operation power supply voltage range: $V_{DD} = 2.65 \text{ V to } 5.50 \text{ V}$
- Low current consumption (Per circuit): $I_{DD} = 200 \mu\text{A typ.}$
- No external parts required for internal phase compensation
- Rail-to-Rail input and output
- Operation temperature range: $Ta = -40^\circ\text{C to +105}^\circ\text{C}$
- Lead-free (Sn 100%), halogen-free
- AEC-Q100 qualified*1

*1. Contact our sales office for details.

■ Applications

- Various sensor interfaces
- High-accuracy current detection
- Strain gauge amplifier

■ Package

- TMSOP-8

■ Block Diagram

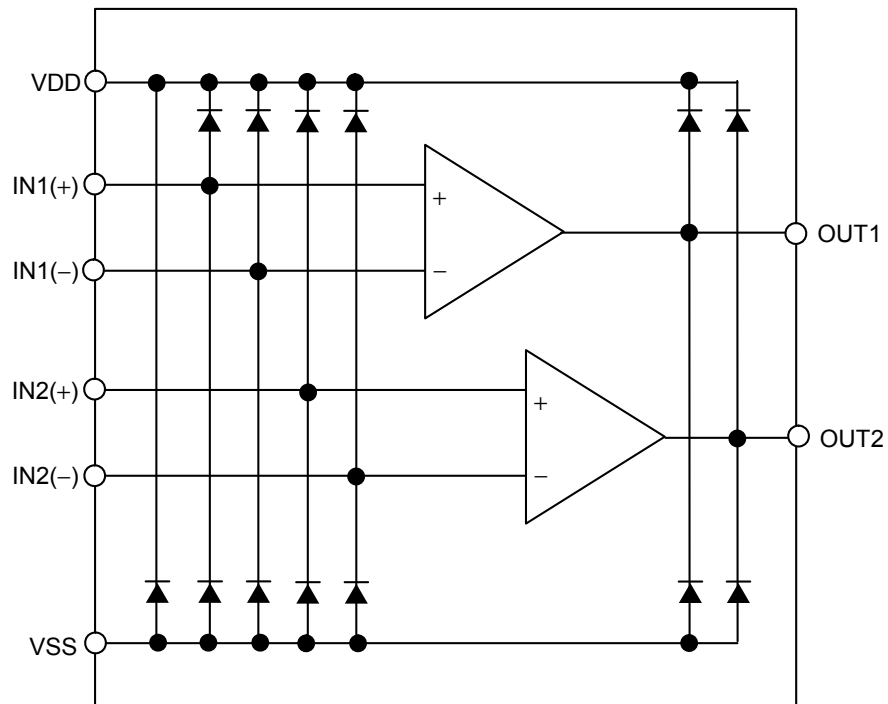


Figure 1

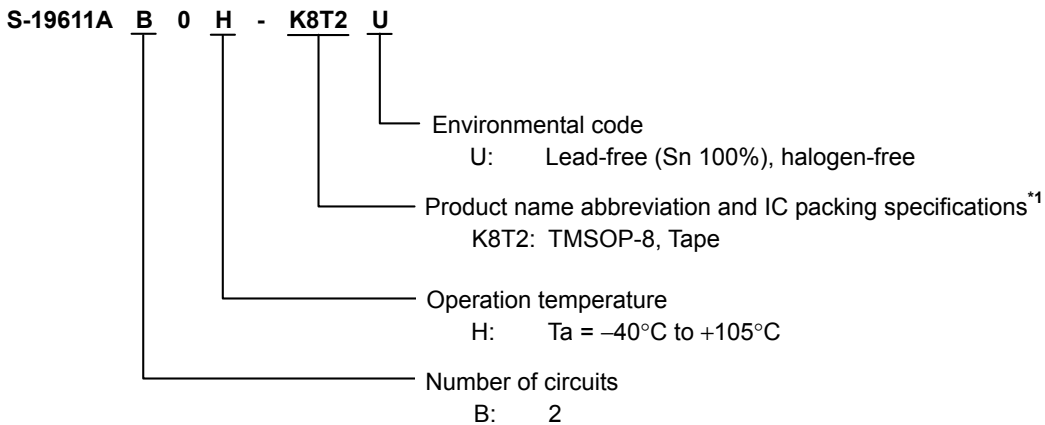
■ **AEC-Q100 Qualified**

This IC supports AEC-Q100 for the operation temperature grade 2.
 Contact our sales office for details of AEC-Q100 reliability specification.

■ **Product Name Structure**

Refer to "1. Product name" regarding the contents of product name, "2. Package" regarding the package drawings and "3. Product name list" regarding the product type.

1. Product name



*1. Refer to the tape drawing.

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel
TMSOP-8	FM008-A-P-SD	FM008-A-C-SD	FM008-A-R-SD

3. Product name list

Table 2

Product Name	Package
S-19611AB0H-K8T2U	TMSOP-8

■ **Pin Configuration**

1. **TMSOP-8**

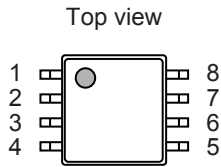


Figure 2

Table 3

Pin No.	Symbol	Description
1	OUT1	Output pin 1
2	IN1(-)	Inverted input pin 1
3	IN1(+)	Non-inverted input pin 1
4	VSS	GND pin
5	IN2(+)	Non-inverted input pin 2
6	IN2(-)	Inverted input pin 2
7	OUT2	Output pin 2
8	VDD	Positive power supply pin

■ Absolute Maximum Ratings

Table 4

(Ta = +25°C unless otherwise specified)

Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltage	V _{DD}	V _{SS} – 0.3 to V _{SS} + 6.0	V
Input voltage	V _{IN(+)} , V _{IN(-)}	V _{SS} – 0.3 to V _{DD} + 0.3	V
Output voltage	V _{OUT}	V _{SS} – 0.3 to V _{DD} + 0.3	V
Differential input voltage	V _{IND}	±5.5	V
Output pin current	I _{SOURCE}	10.0	mA
	I _{SINK}	10.0	mA
Operation ambient temperature	T _{opr}	–40 to +105	°C
Storage temperature	T _{stg}	–55 to +125	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Thermal Resistance Value

Table 5

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Junction-to-ambient thermal resistance*1	θ _{ja}	TMSOP-8	Board 1	–	160	–	°C/W
			Board 2	–	133	–	°C/W

*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ Thermal Characteristics" for details of power dissipation and test board.

■ Electrical Characteristics

Table 6

DC Electrical Characteristics (V_{DD} = 5.0 V, Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Operation power supply voltage range	V _{DD}	Ta = -40°C to +105°C	2.65	5.00	5.50	V	-
Current consumption (2 circuits)	I _{DD}	V _{CMR} = V _{OUT} = V _{DD} / 2, Ta = -40°C to +105°C	-	400	600	μA	5
Input offset voltage	V _{IO}	V _{CMR} = V _{DD} / 2	-17	±1	+17	μV	1
		V _{CMR} = V _{DD} / 2, Ta = -40°C to +105°C	-100	±1	+100	μV	1
Input offset voltage drift	$\frac{\Delta V_{IO}}{\Delta T_a}$	V _{CMR} = V _{DD} / 2, Ta = -40°C to +105°C	-	±0.1	-	μV/°C	1
Input offset current	I _{IO}	-	-	±140	-	pA	-
		Ta = -40°C to +105°C	-	±300	-	pA	-
Input bias current	I _{BIAS}	-	-	±70	-	pA	-
		Ta = -40°C to +105°C	-	±3000	-	pA	-
Common-mode input voltage range	V _{CMR}	Ta = -40°C to +105°C	V _{SS} - 0.1	-	V _{DD} + 0.1	V	2
Voltage gain (open loop)	A _{VOL}	V _{SS} + 0.1 V ≤ V _{OUT} ≤ V _{DD} - 0.1 V, V _{CMR} = V _{DD} / 2, R _L = 10 kΩ, Ta = -40°C to +105°C	106	130	-	dB	8
Maximum output swing voltage	V _{OH}	R _L = 10 kΩ, Ta = -40°C to +105°C	4.9	-	-	V	3
	V _{OL}	R _L = 10 kΩ, Ta = -40°C to +105°C	-	-	0.1	V	4
Common-mode input signal rejection ratio	CMRR	V _{SS} - 0.1 V ≤ V _{CMR} ≤ V _{DD} + 0.1 V, Ta = -40°C to +105°C	100	130	-	dB	2
Power supply voltage rejection ratio	PSRR	V _{DD} = 2.65 V to 5.50 V, Ta = -40°C to +105°C	95	120	-	dB	1
Source current	I _{SOURCE}	V _{OUT} = V _{DD} - 0.1 V, Ta = -40°C to +105°C	0.8	2.5	-	mA	6
Sink current	I _{SINK}	V _{OUT} = 0.1 V, Ta = -40°C to +105°C	1.0	2.9	-	mA	7

Table 7

AC Electrical Characteristics (V_{DD} = 5.0 V, Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Slew rate	SR	R _L = 1.0 MΩ, C _L = 15 pF (Refer to Figure 11)	-	0.22	-	V/μs
Gain-bandwidth product	GBP	C _L = 0 pF	-	320	-	kHz

■ Test Circuits (Per circuit)

1. Power supply voltage rejection ratio, input offset voltage

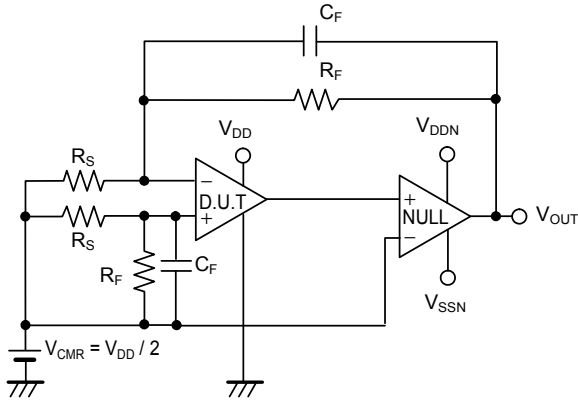


Figure 3 Test Circuit 1

• Power supply voltage rejection ratio (PSRR)

The power supply voltage rejection ratio (PSRR) can be calculated by the following expression, with V_{OUT} measured at each V_{DD} .

Test conditions:

$$V_{DD} = 2.65 \text{ V: } V_{DD} = V_{DD1}, V_{OUT} = V_{OUT1}$$

$$V_{DD} = 5.50 \text{ V: } V_{DD} = V_{DD2}, V_{OUT} = V_{OUT2}$$

$$PSRR = 20 \log \left(\left| \frac{V_{DD1} - V_{DD2}}{\left(V_{OUT1} - \frac{V_{DD1}}{2} \right) - \left(V_{OUT2} - \frac{V_{DD2}}{2} \right)} \right| \times \frac{R_F + R_S}{R_S} \right)$$

• Input offset voltage (V_{IO})

$$V_{IO} = \left(V_{OUT} - \frac{V_{DD}}{2} \right) \times \frac{R_S}{R_F + R_S}$$

2. Common-mode input signal rejection ratio, common-mode input voltage range

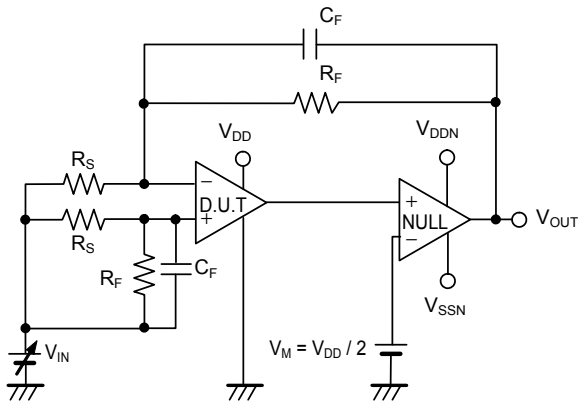


Figure 4 Test Circuit 2

• Common-mode input signal rejection ratio (CMRR)

The common-mode input signal rejection ratio (CMRR) can be calculated by the following expression, with V_{OUT} measured at each V_{IN} .

Test conditions:

$$V_{IN} = V_{CMR \text{ Max.}}: V_{IN} = V_{IN1}, V_{OUT} = V_{OUT1}$$

$$V_{IN} = V_{CMR \text{ Min.}}: V_{IN} = V_{IN2}, V_{OUT} = V_{OUT2}$$

$$CMRR = 20 \log \left(\left| \frac{V_{IN1} - V_{IN2}}{\left(V_{OUT1} - V_{IN1} \right) - \left(V_{OUT2} - V_{IN2} \right)} \right| \times \frac{R_F + R_S}{R_S} \right)$$

• Common-mode input voltage range (V_{CMR})

The common-mode input voltage range is the range of V_{IN} in which V_{OUT} satisfies the common-mode input signal rejection ratio specifications.

3. Maximum output swing voltage

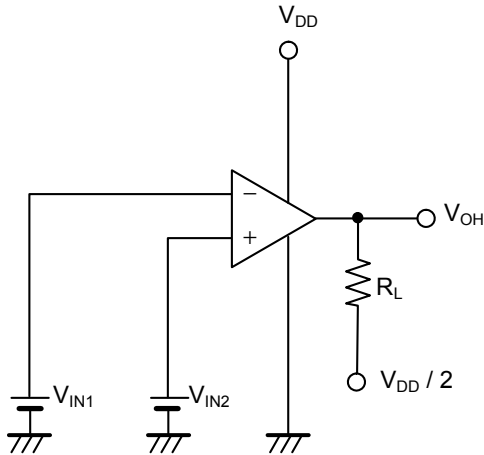


Figure 5 Test Circuit 3

• **Maximum output swing voltage (V_{OH})**

Test conditions:

$$V_{IN1} = \frac{V_{DD}}{2} - 0.1 \text{ V}$$

$$V_{IN2} = \frac{V_{DD}}{2} + 0.1 \text{ V}$$

$$R_L = 10 \text{ k}\Omega$$

4. Maximum output swing voltage

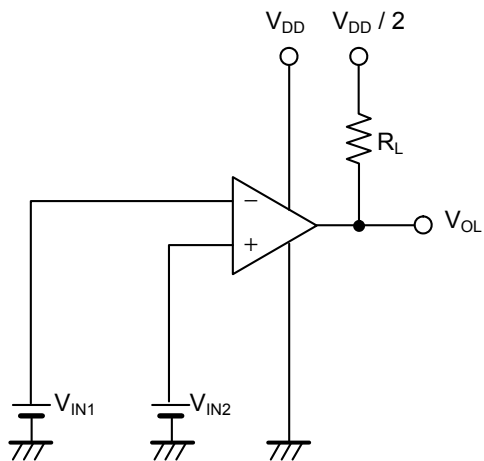


Figure 6 Test Circuit 4

• **Maximum output swing voltage (V_{OL})**

Test conditions:

$$V_{IN1} = \frac{V_{DD}}{2} + 0.1 \text{ V}$$

$$V_{IN2} = \frac{V_{DD}}{2} - 0.1 \text{ V}$$

$$R_L = 10 \text{ k}\Omega$$

5. Current consumption

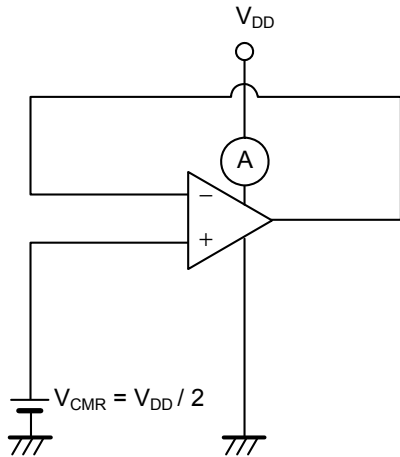


Figure 7 Test Circuit 5

• **Current consumption (I_{DD})**

6. Source current

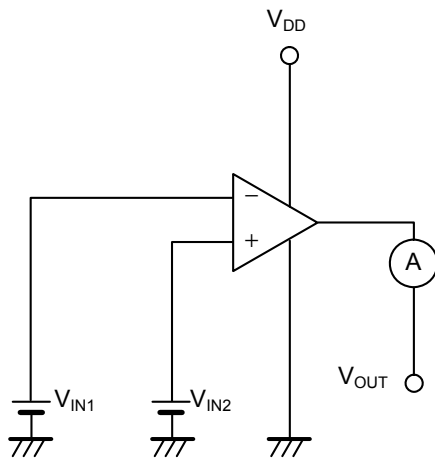


Figure 8 Test Circuit 6

• **Source current (I_{SOURCE})**

Test conditions:

$$V_{OUT} = V_{DD} - 0.1 \text{ V}$$

$$V_{IN1} = \frac{V_{DD}}{2} - 0.1 \text{ V}$$

$$V_{IN2} = \frac{V_{DD}}{2} + 0.1 \text{ V}$$

7. Sink current

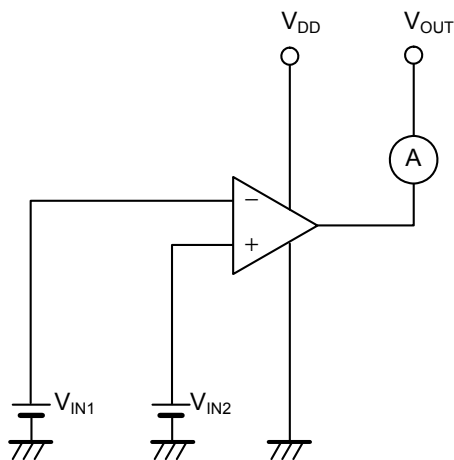


Figure 9 Test Circuit 7

• **Sink current (I_{SINK})**

Test conditions:

$$V_{OUT} = 0.1 \text{ V}$$

$$V_{IN1} = \frac{V_{DD}}{2} + 0.1 \text{ V}$$

$$V_{IN2} = \frac{V_{DD}}{2} - 0.1 \text{ V}$$

8. Voltage gain

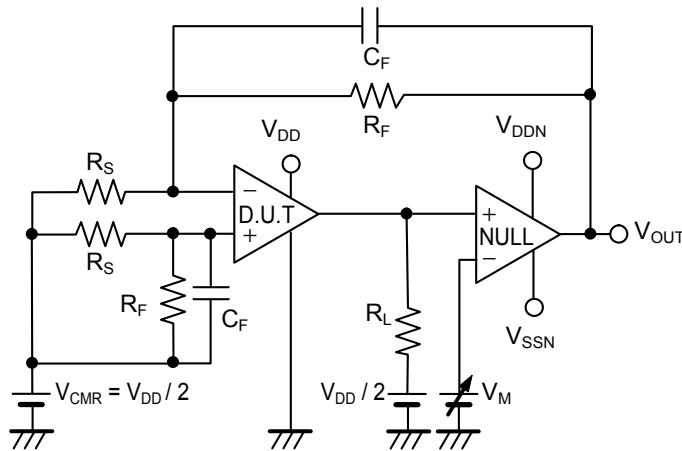


Figure 10 Test Circuit 8

• Voltage gain (open loop) (A_{VOL})

The voltage gain (A_{VOL}) can be calculated by the following expression, with V_{OUT} measured at each V_M .

Test conditions:

$$V_M = V_{DD} - 0.1 \text{ V: } V_M = V_{M1}, V_{OUT} = V_{OUT1}$$

$$V_M = 0.1 \text{ V: } V_M = V_{M2}, V_{OUT} = V_{OUT2}$$

$$A_{VOL} = 20 \log \left(\left| \frac{V_{M1} - V_{M2}}{V_{OUT1} - V_{OUT2}} \right| \times \frac{R_F + R_S}{R_S} \right)$$

$$R_L = 10 \text{ k}\Omega$$

9. Slew rate

Measured by the voltage follower circuit.

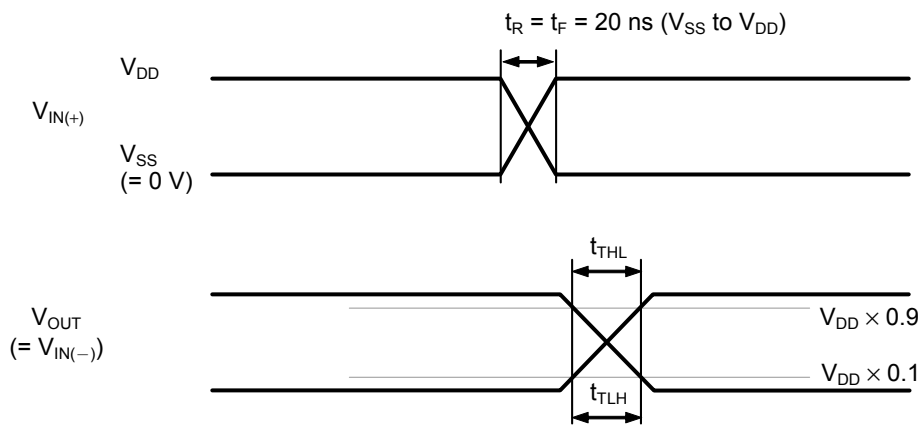


Figure 11

• Slew rate (SR)

When falling

$$SR = \frac{V_{DD} \times 0.8}{t_{THL}}$$

When rising

$$SR = \frac{V_{DD} \times 0.8}{t_{TLH}}$$

■ Usage Examples

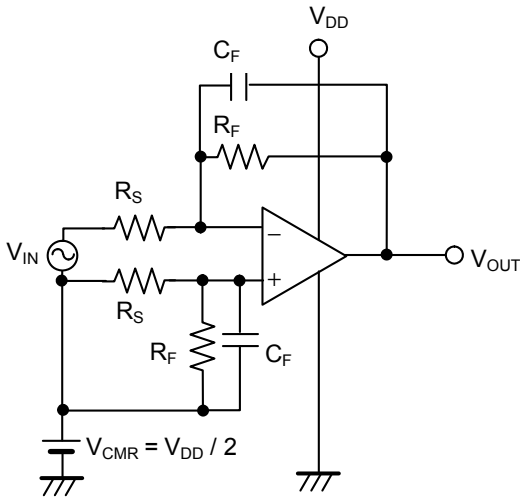


Figure 12 Differential Amplifier Circuit

[Example of Gain = 1000 times]

$R_S = 1 \text{ k}\Omega$
 $R_F = 1 \text{ M}\Omega$
 $C_F = 1000 \text{ pF}$

[Example of Gain = 100 times]

$R_S = 1 \text{ k}\Omega$
 $R_F = 100 \text{ k}\Omega$
 $C_F = 1000 \text{ pF}$

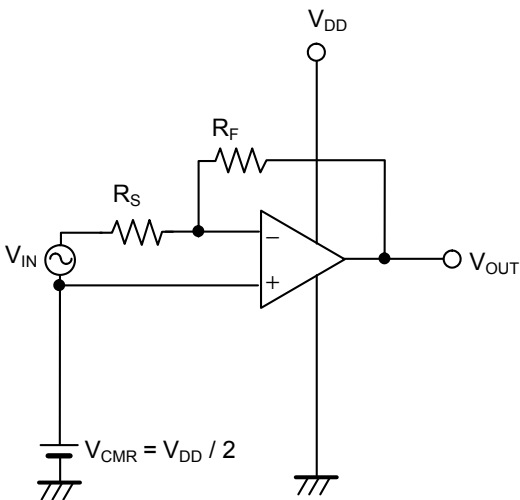


Figure 13 Inverting Amplifier Circuit

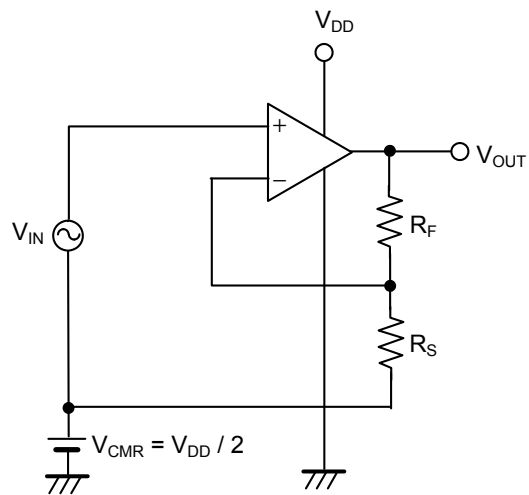


Figure 14 Non-inverting Amplifier Circuit

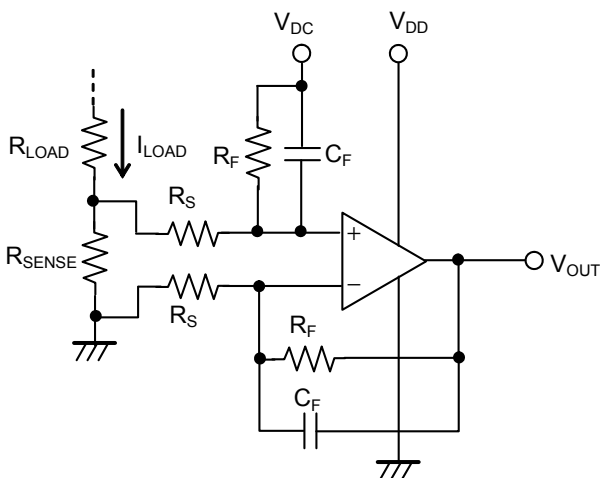


Figure 15 Low-side Current Detection Circuit

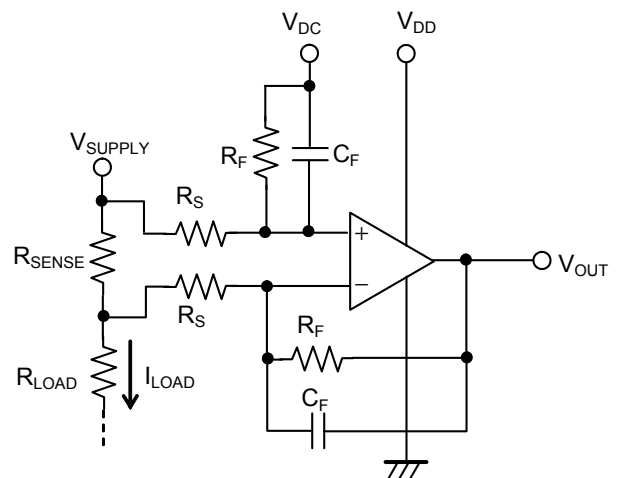


Figure 16 High-side Current Detection Circuit

Caution The above connection diagram and constant will not guarantee successful operation. Perform through evaluation using the actual application to set the constant.

■ Precautions

- Generally an operational amplifier may cause oscillation depending on the selection of external parts. Perform thorough evaluation using the actual application to set the constant.
- Do not apply an electrostatic discharge to this IC that exceeds performance ratings of the built-in electrostatic protection circuit.
- SII Semiconductor Corporation claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.
- Use this IC with the output current of 10 mA or less.
- When the output voltage is used in the range of $V_{DD} - 100$ mV or more, or $V_{SS} + 100$ mV or less, the operation may become unstable depending on the circuit configuration. Contact our sales office for details.
- When using the voltage follower circuit (Gain = 1 time), insert a resistor of $470\ \Omega$ or more for the stable operation, as shown in **Figure 17**. The operation may be unstable depending on the value of the load capacitance connected to the output pin, even when the voltage follower circuit is not used. Use the product under thorough evaluation.

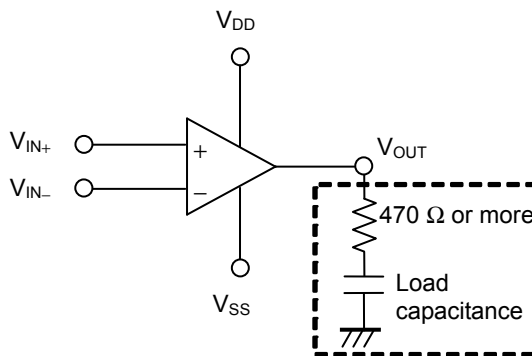
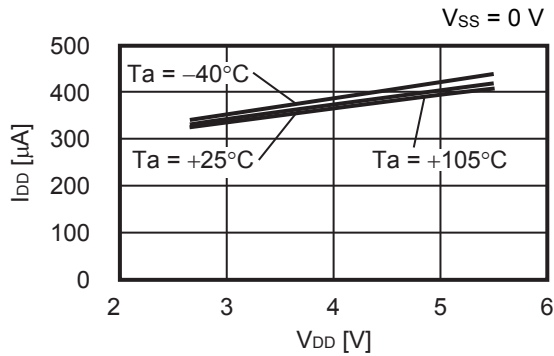


Figure 17

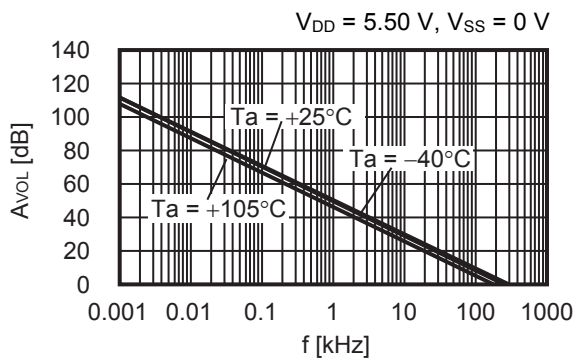
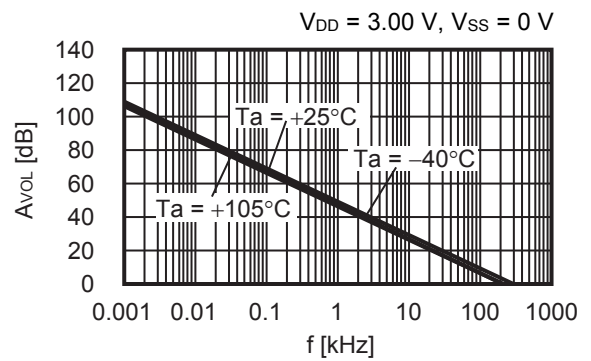
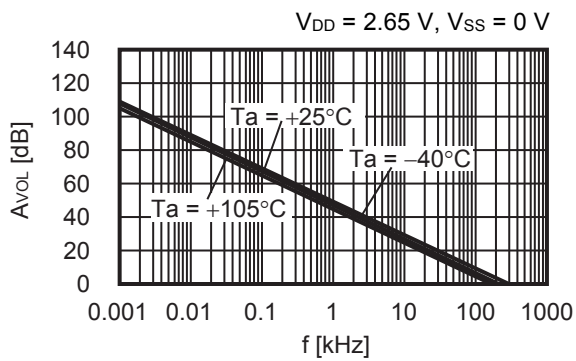
Caution The above connection diagram and constant will not guarantee successful operation. Perform through evaluation using the actual application to set the constant.

■ Characteristics (Typical Data)

1. Current consumption (I_{DD}) (2 circuits) vs. Power supply voltage (V_{DD})

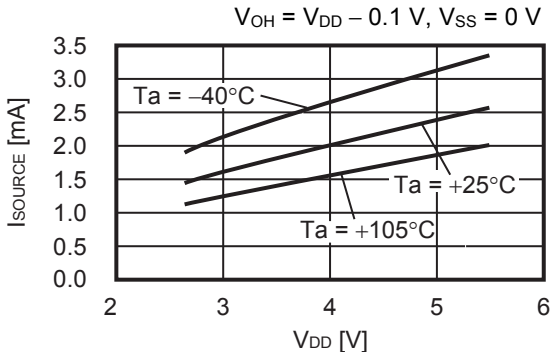


2. Voltage gain (A_{VOL}) vs. Frequency (f)

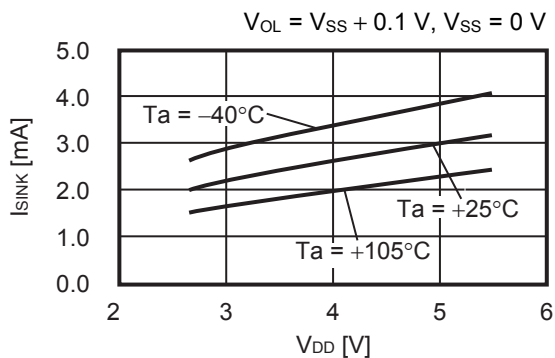


3. Output current

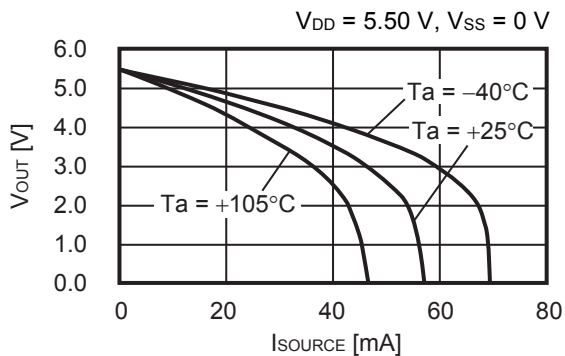
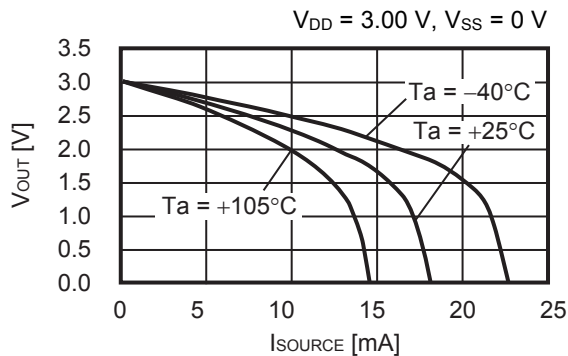
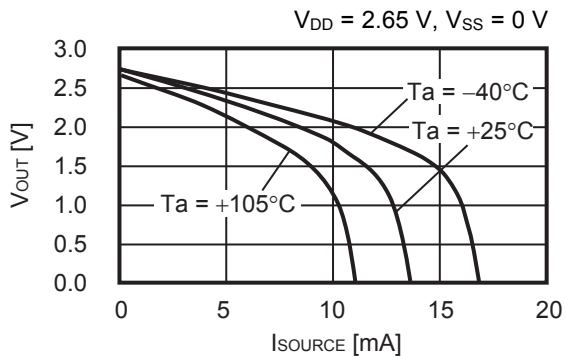
3.1 Source current (I_{SOURCE}) vs. Power supply voltage (V_{DD})



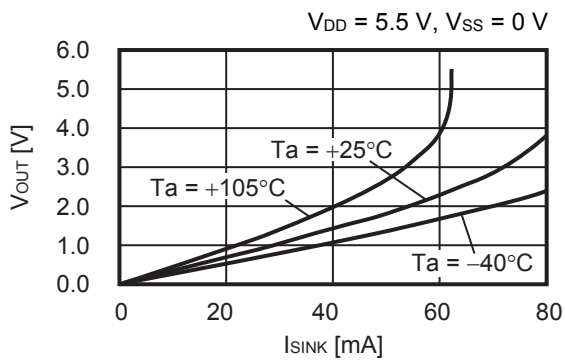
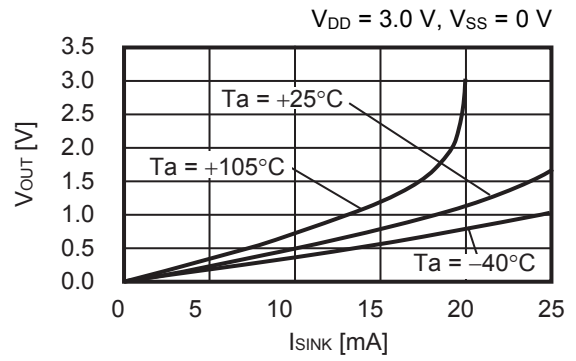
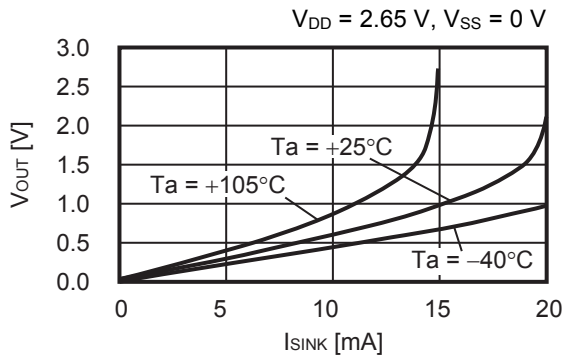
3.2 Sink current (I_{SINK}) vs. Power supply voltage (V_{DD})



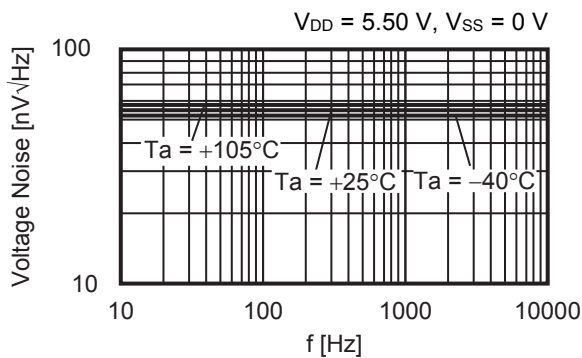
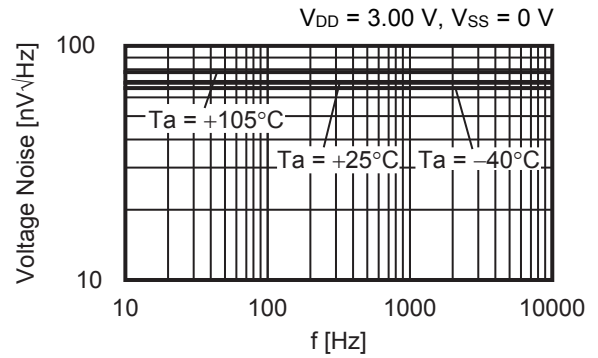
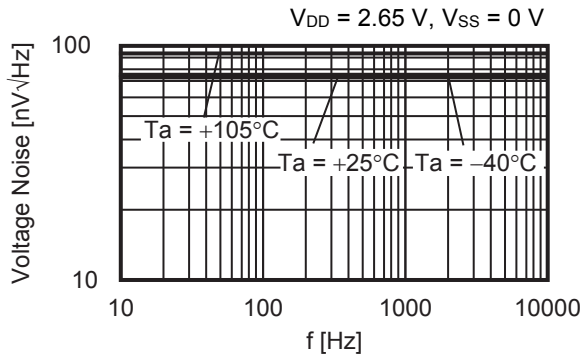
3.3 Output voltage (V_{OUT}) vs. Source current (I_{SOURCE})



3. 4 Output voltage (V_{OUT}) vs. Sink current (I_{SINK})



4. Input-referred noise voltage vs. Frequency (f)



■ Thermal Characteristics

1. TMSOP-8

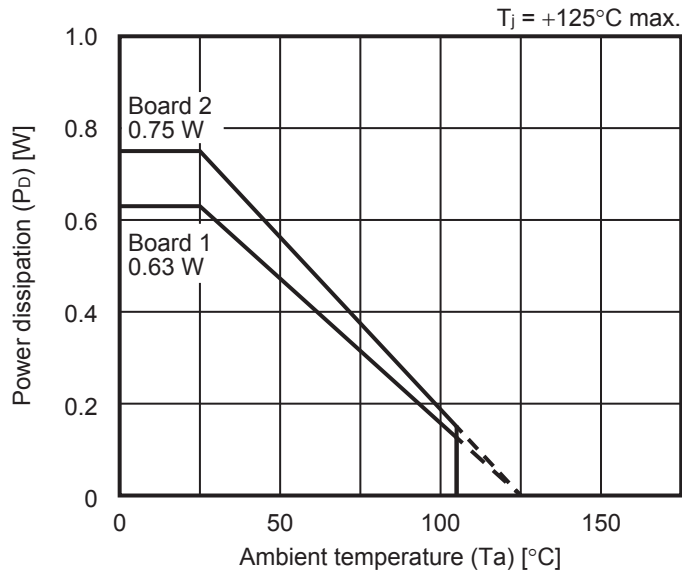


Figure 18 Power Dissipation of Package (When Mounted on Board)

1.1 Board 1

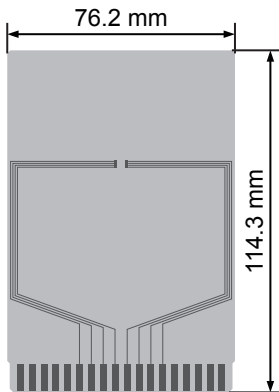


Figure 19

Table 8

Item	Specification
Thermal resistance value (θ_{ja})	160°C/W
Size	114.3 mm × 76.2 mm × t1.6 mm
Material	FR-4
Number of copper foil layer	2
Copper foil layer	1 Land pattern and wiring for testing: t0.070 mm
	2 -
	3 -
	4 74.2 mm × 74.2 mm × t0.070 mm
Thermal via	-

1.2 Board 2

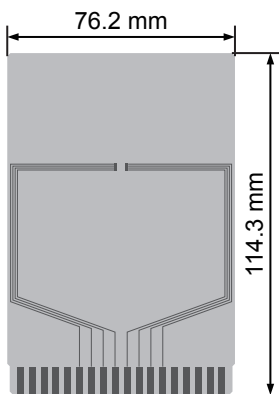
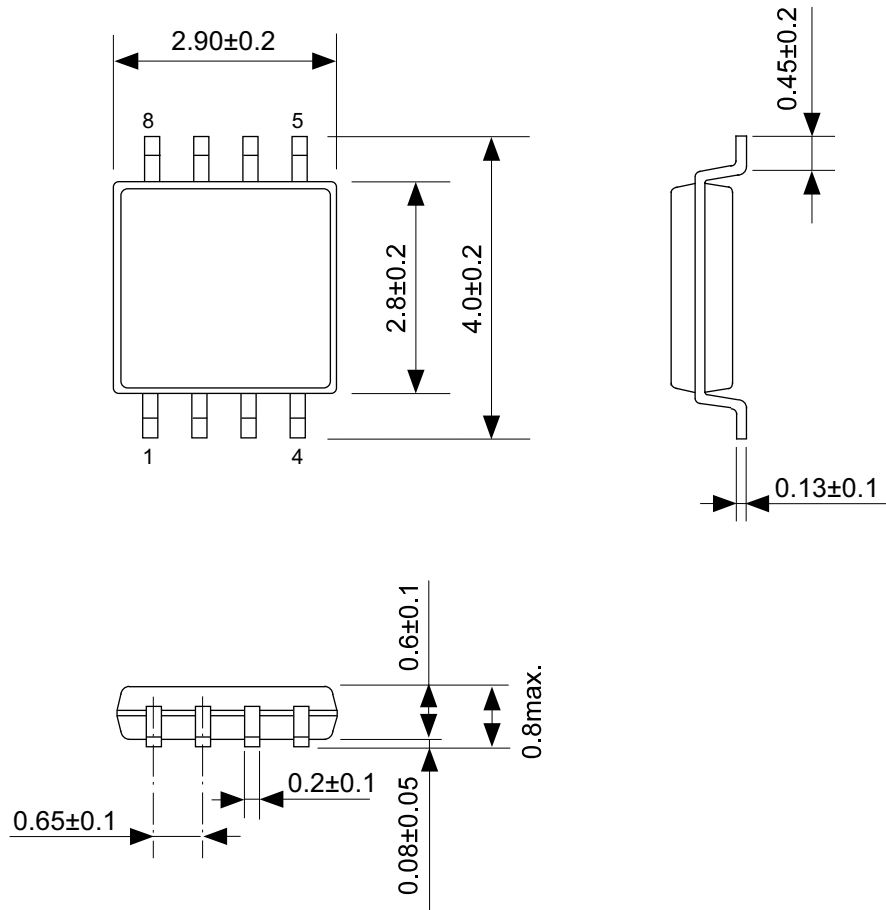


Figure 20

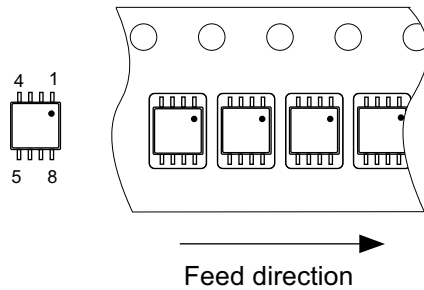
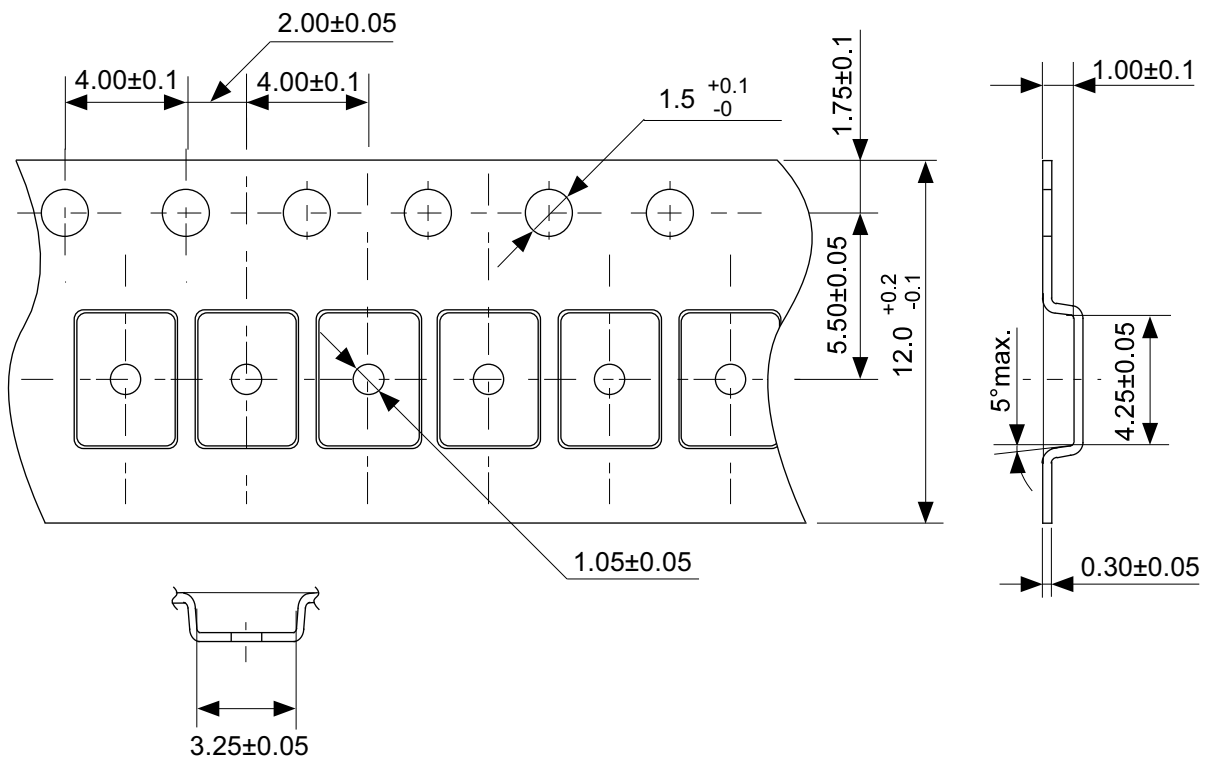
Table 9

Item	Specification
Thermal resistance value (θ_{ja})	133°C/W
Size	114.3 mm × 76.2 mm × t1.6 mm
Material	FR-4
Number of copper foil layer	4
Copper foil layer	1 Land pattern and wiring for testing: t0.070 mm
	2 74.2 mm × 74.2 mm × t0.035 mm
	3 74.2 mm × 74.2 mm × t0.035 mm
	4 74.2 mm × 74.2 mm × t0.070 mm
Thermal via	-



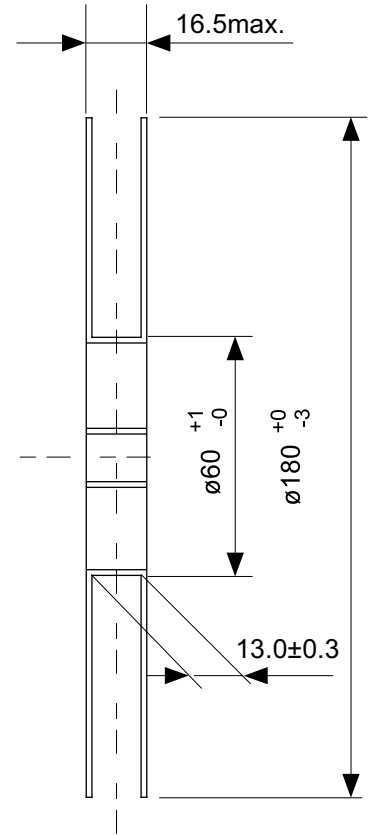
No. FM008-A-P-SD-1.1

TITLE	TMSOP8-A-PKG Dimensions
No.	FM008-A-P-SD-1.1
SCALE	
UNIT	mm
SII Semiconductor Corporation	

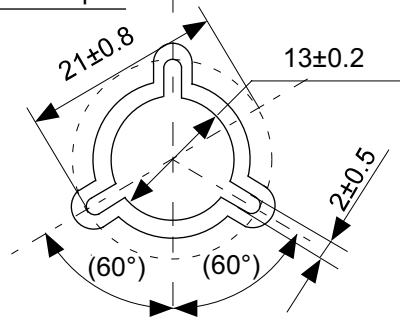


No. FM008-A-C-SD-2.0

TITLE	TMSOP8-A-Carrier Tape
No.	FM008-A-C-SD-2.0
SCALE	
UNIT	mm
SII Semiconductor Corporation	



Enlarged drawing in the central part



No. FM008-A-R-SD-1.0

TITLE	TMSOP8-A-Reel		
No.	FM008-A-R-SD-1.0		
SCALE		QTY.	4,000
UNIT	mm		
SII Semiconductor Corporation			

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